L Number	Hits	Search Text	DB	Time stamp
2	44	resin near10 (polish\$4 or grind\$) near10 thick\$ same (back or back\$1side or rear) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/19 11:26
5	133	(resin near10 (polish\$4 or grind\$) near10 (back or back\$1side or rear) and semiconductor) not (resin near10 (polish\$4 or grind\$) near10 thick\$ same (back or back\$1side or rear) and	JBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19
6	7	semiconductor) resin near10 (polish\$4 or grind\$) near10 thick\$ same bottom and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 11:28
7	54	resin near10 (polish\$4 or grind\$) near10 bottom and semiconductor not (resin near10 (polish\$4 or grind\$) near10 thick\$ same bottom and semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 11:49
31	150	etch\$ near10 (grind\$ or polish\$) near10 resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 13:03
32	94	etch\$ near10 (grind\$ or polish\$) near10 resin and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 13:05
33	38	(etch\$ near10 (grind\$ or polish\$) near10 resin and @py<2002) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 13:06
1	120	resin near10 (back or back\$lsid\$) near10 (polish\$ or grind\$) and semiconduct\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/17
-	68	semiconductor near3 chip and resin same electrode same (polish\$ or grind\$) same (rear or back)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/17 14:30
-	30	semiconductor near3 chip same resin same electrode same (polish\$ or grind\$) same (rear or back)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/17 15:20
-	10	semiconductor near3 chip near10 active same resin same (polish\$ or grind\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/17 15:57
-	24	(sekine.in. adj kenji) and chip same substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/17 15:57
-	50	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$lside) same electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 16:56

	70	resin near10 (polish\$ or grind\$) near10	USPAT;	2003/11/18
	, ,	(rear or back or back\$lside) same chip	US-PGPUB;	17:28
		(Lear or pass or passes)	EPO; JPO;	
	ł		DERWENT;	İ
	i		IBM TDB	
		ichikawa.in. near2 kimiya and resin same	USPĀT;	2003/11/18
	3	semi conductor	US-PGPUB;	17:22
		Semiconadoros	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	46	resin near10 (polish\$ or grind\$) near10	USPAT;	2003/11/18
	10	(rear or back or back\$1side) near20	US-PGPUB;	17:53
		expos\$	EPO; JPO;	
		exposy	DERWENT;	
			IBM TDB	
	131	resin near10 (polish\$ or grind\$) near10	USPAT;	2003/11/18
	151	(rear or back or back\$1side) and chip	US-PGPUB;	18:12
		(lear or pack or packyrbracy and surp	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	34	(resin near10 (polish\$ or grind\$) near10	USPAT:	2003/11/19
	51	(rear or back or back\$1side) and chip)	US-PGPUB;	10:17
		not ((resin near10 (polish\$ or grind\$)	EPO; JPO;	
		near10 (rear or back or back\$1side) same	DERWENT;	
		electrode) or (resin near10 (polish\$ or	IBM TDB	
		grind\$) near10 (rear or back or		
		back\$lside) same chip) or (resin near10		
		(polish\$ or grind\$) near10 (rear or back		1
		or back\$1side) near20 expos\$))		